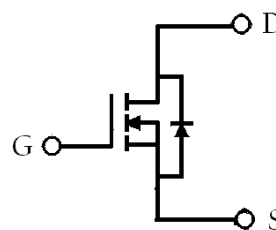
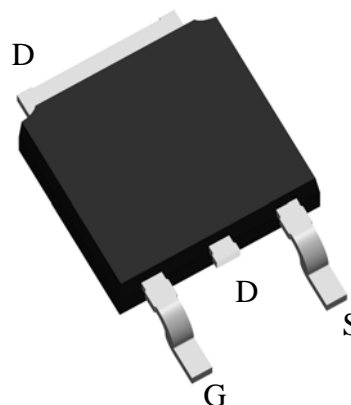


N -Channel Enhancement Mode Power MOSFET

Features:

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating and halogen-free package

TO-252(DPAK)



G : Gate D : Drain S : Source

BV_{DSS}	60V
I_D @ V_{GS}=10V, T_C=25°C	56A
R_{DS(ON)}@ V_{GS}=10V, I_D=20A	6.0mΩ (typ)
R_{DS(ON)}@ V_{GS}=4.5V, I_D=15A	9.5mΩ (typ)

Ordering Information

Device	Package	Shipping
KJB7D0N06R	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel

Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ T _C =25°C, V _{GS} =10V	I _D	56	A
Continuous Drain Current @ T _C =100°C, V _{GS} =10V		35.4	
Continuous Drain Current @ T _A =25°C, V _{GS} =10V *2	I _{DSM}	12.7	
Continuous Drain Current @ T _A =100°C, V _{GS} =10V *2		8.0	
Continuous Drain Current @ T _A =25°C, V _{GS} =10V *3		10.2	
Continuous Drain Current @ T _A =100°C, V _{GS} =10V *3		6.5	
Pulsed Drain Current *1	I _{DM}	224	
Avalanche Current @ L=0.1mH	I _{AS}	48	mJ
Avalanche Energy @ L=1mH, I _D =20A, V _{DD} =25V *4	E _{AS}	200	
Total Power Dissipation @ T _C =25°C	P _D	50	W
Total Power Dissipation @ T _C =100°C		20	
Total Power Dissipation @ T _A =25°C *2	P _{DSM}	2.5	
Total Power Dissipation @ T _A =100°C *2		1.0	
Total Power Dissipation @ T _A =25°C *3		1.7	
Total Power Dissipation @ T _A =100°C *3		0.7	
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{th,j-c}	2.5	°C/W
Thermal Resistance, Junction-to-ambient, max *2	R _{th,j-a}	50	
Thermal Resistance, Junction-to-ambient, max *3		75	

Note : *1. Pulse width limited by maximum junction temperature

*2. When the device is mounted on 1 in² FR-4 board with 2 oz. copper.

*3. When the device is on the minimum pad size recommended.

*4. 100% tested by conditions of L=0.1mH, I_{AS}=20A, V_{GS}=10V, V_{DD}=25V.

*5. The power dissipation P_D is based on T_j(MAX)=150 °C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

*6. The power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150 °C. The value in any given application depends on the user's specific board design.

Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	60	-	-	V	V _{GS} =0V, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.03	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	1	-	2.5	V	V _{DS} =V _{GS} , I _D =250μA
G _{FS} *1	-	21.3	-	S	V _{DS} =5V, I _D =10A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V

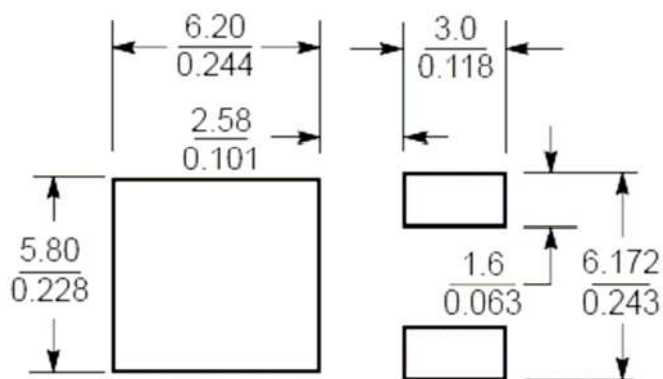
IDSS	-	-	1	μA	VDS =48V, VGS =0V
	-	-	25		VDS =48V, VGS =0V, Tj=125°C
RDS(ON) *1	-	6.0	8	mΩ	VGS =10V, ID=20A
	-	9.5	13.5		VGS =4.5V, ID=15A
Dynamic					
Qg *1, 2	-	46.9	-	nC	VDS=48V, VGS=10V, ID=20A
Qgs *1, 2	-	9.5	-		
Qgd *1, 2	-	9.6	-		
td(ON) *1, 2	-	17.6	-	ns	VDS=30V, ID=20A, VGS=10V, RGS=3Ω
tr *1, 2	-	17.4	-		
td(OFF) *1, 2	-	54.6	-		
tf *1, 2	-	10	-		
Ciss	-	2751	-	pF	VGS=0V, VDS=30V, f=1MHz
Coss	-	358	-		
Crss	-	41	-		
Rg	-	1.8	-	Ω	f=1MHz
Source-Drain Diode					
IS *1	-	-	40	A	
ISM *3	-	-	160		
VSD *1	-	0.87	1.2	V	IS=20A, VGS=0V
trr	-	23.5	-	ns	IF=20A, dIF/dt=100A/μs
Qrr	-	18.5	-	nC	

Note : *1.Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

*2.Independent of operating temperature

*3.Pulse width limited by maximum junction temperature.

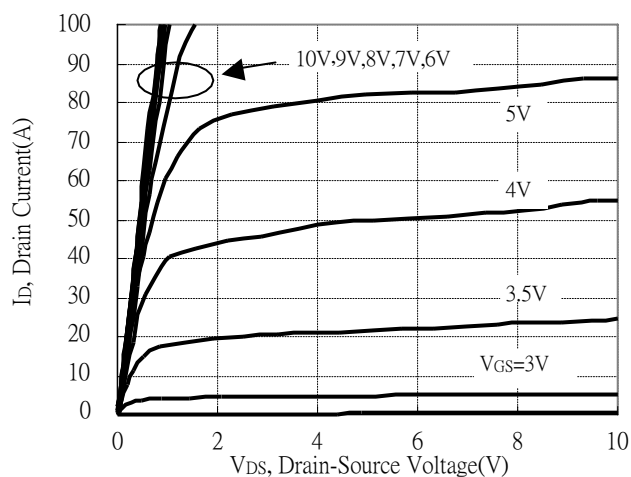
Recommended soldering footprint



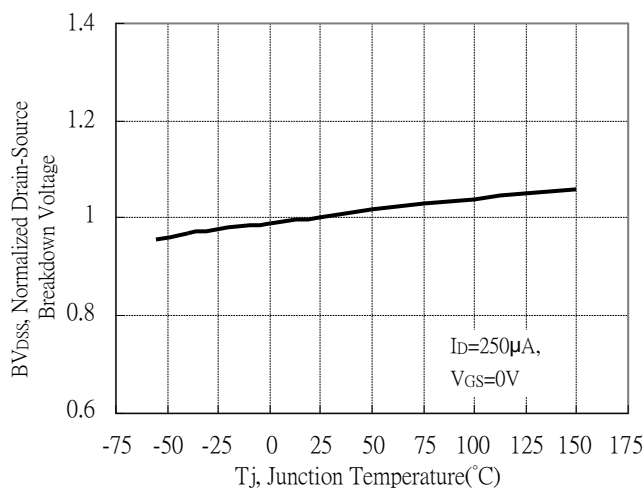
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

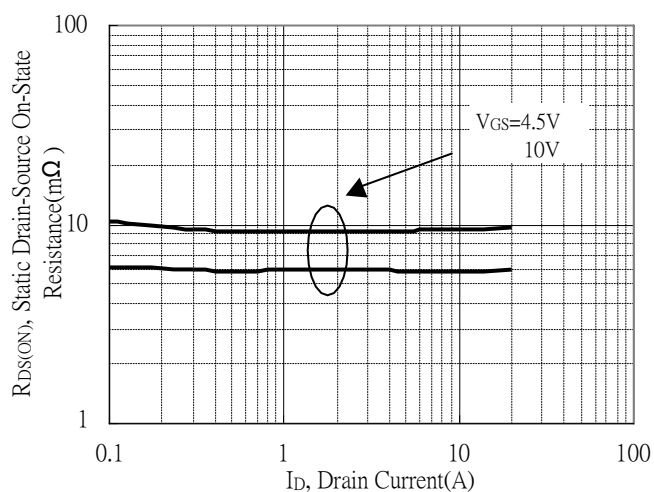
Typical Output Characteristics



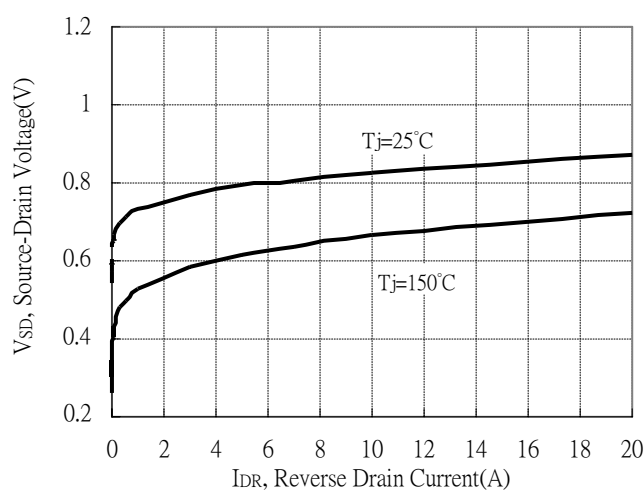
Breakdown Voltage vs Ambient Temperature



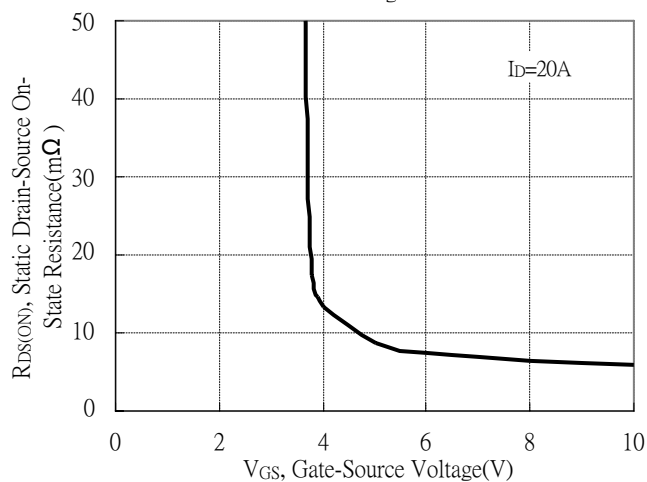
Static Drain-Source On-State resistance vs Drain Current



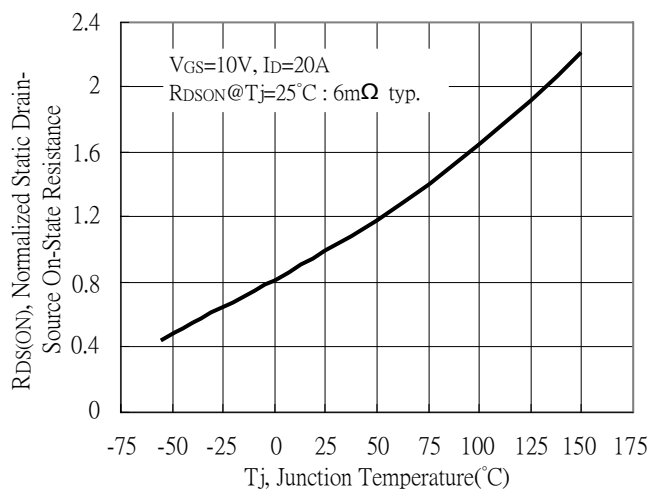
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

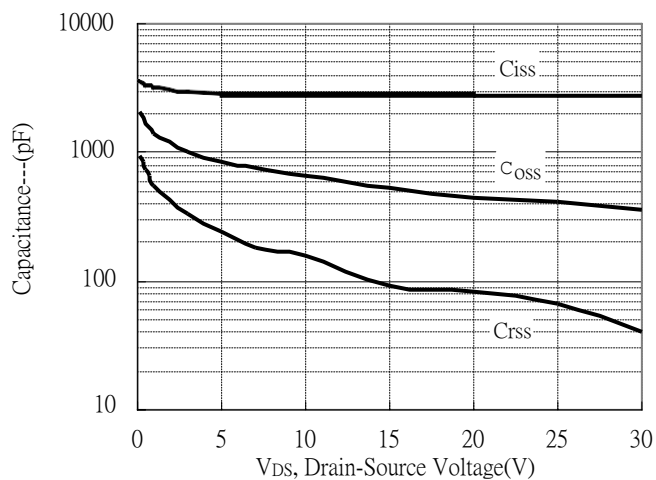


Drain-Source On-State Resistance vs Junction Temperature

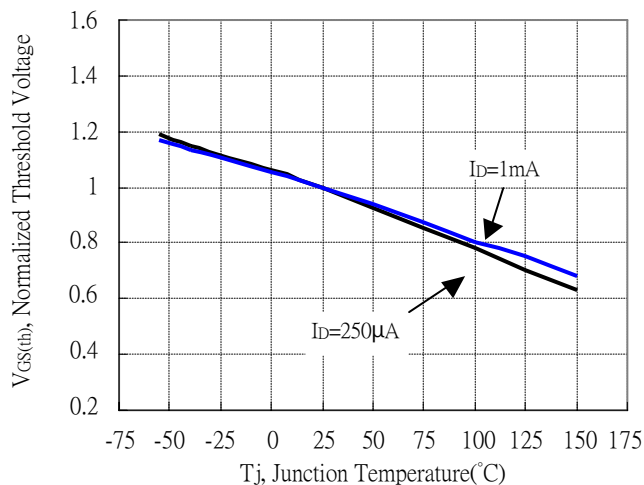


Typical Characteristics(Cont.)

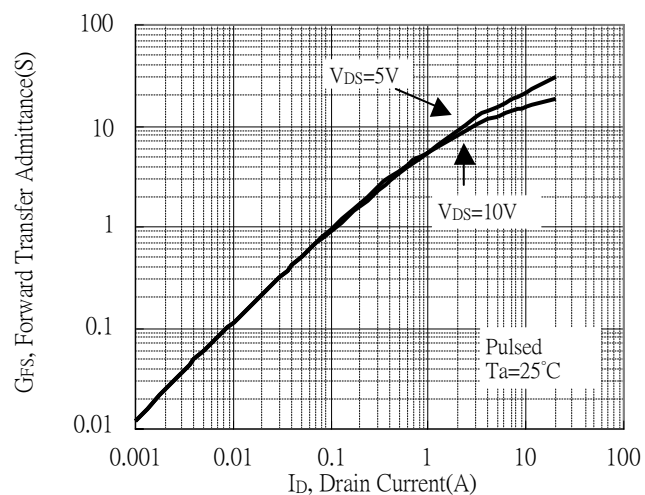
Capacitance vs Drain-to-Source Voltage



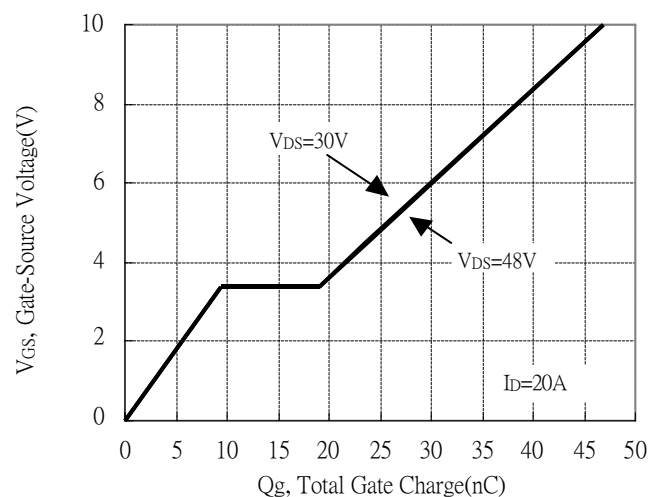
Threshold Voltage vs Junction Temperature



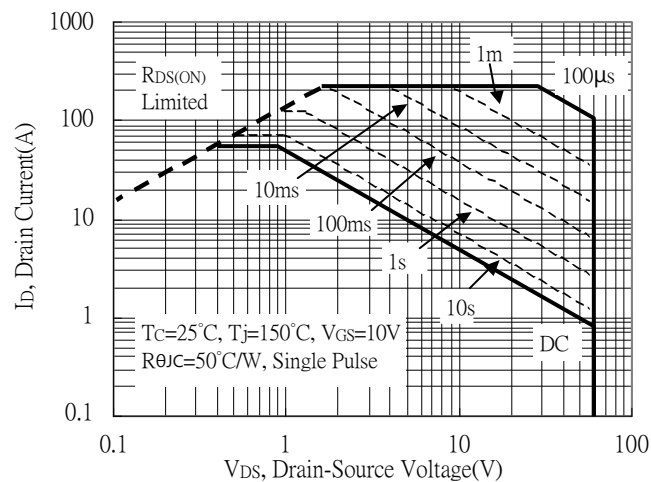
Forward Transfer Admittance vs Drain Current



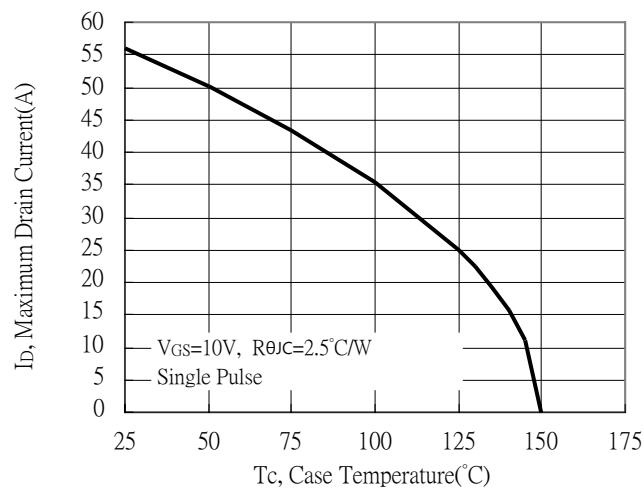
Gate Charge Characteristics



Maximum Safe Operating Area

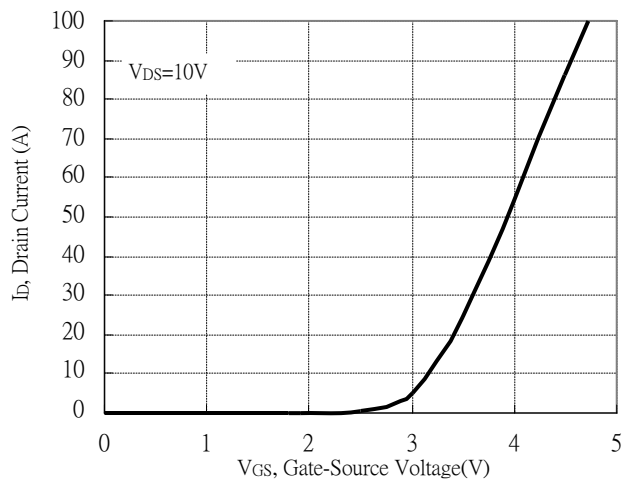


Maximum Drain Current vs Case Temperature

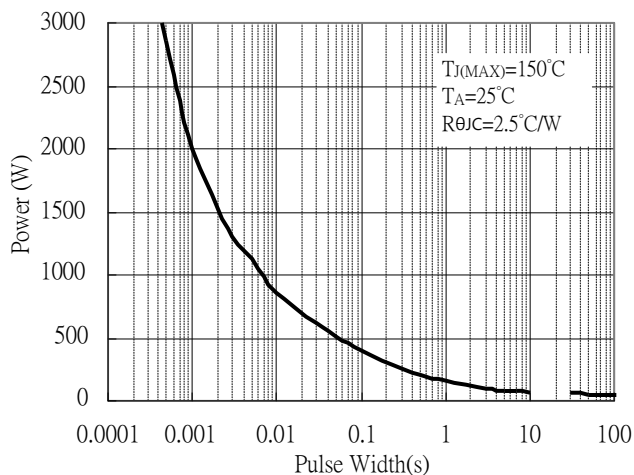


Typical Characteristics(Cont.)

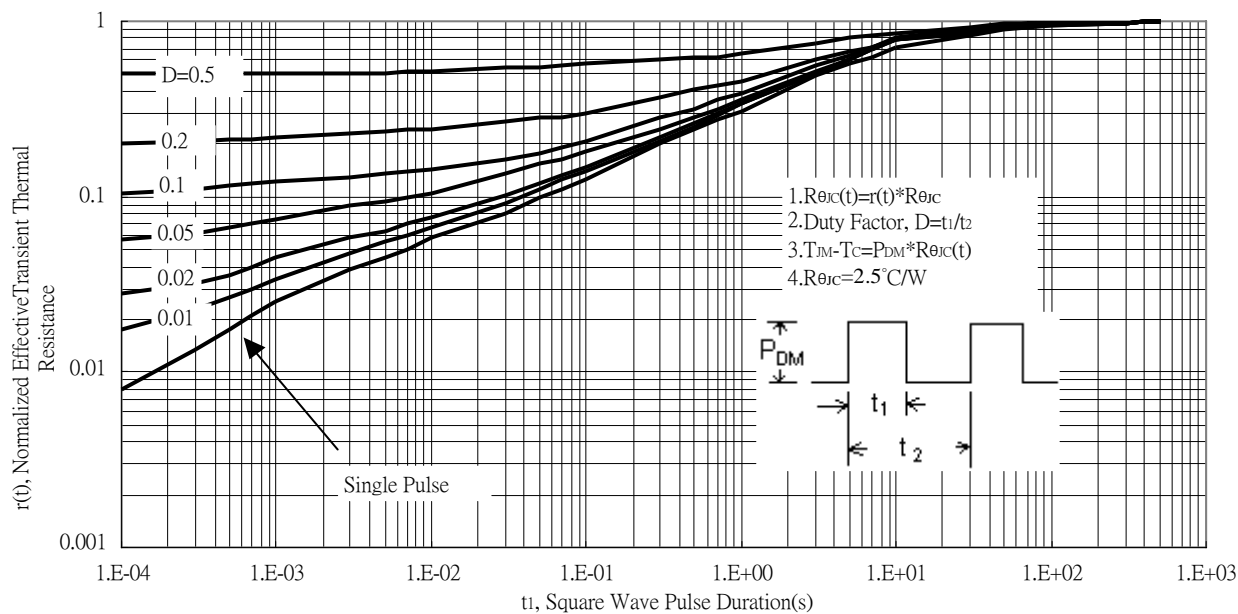
Typical Transfer Characteristics



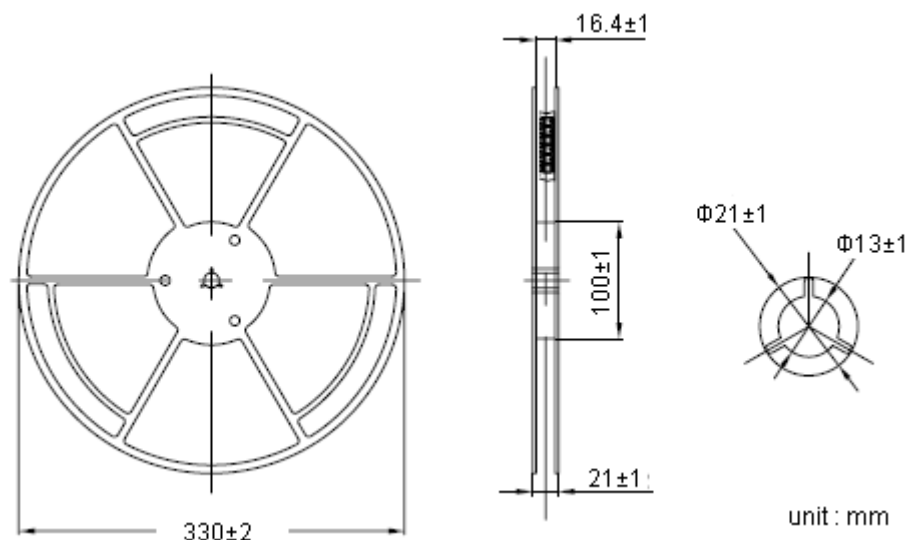
Single Pulse Power Rating, Junction to Case



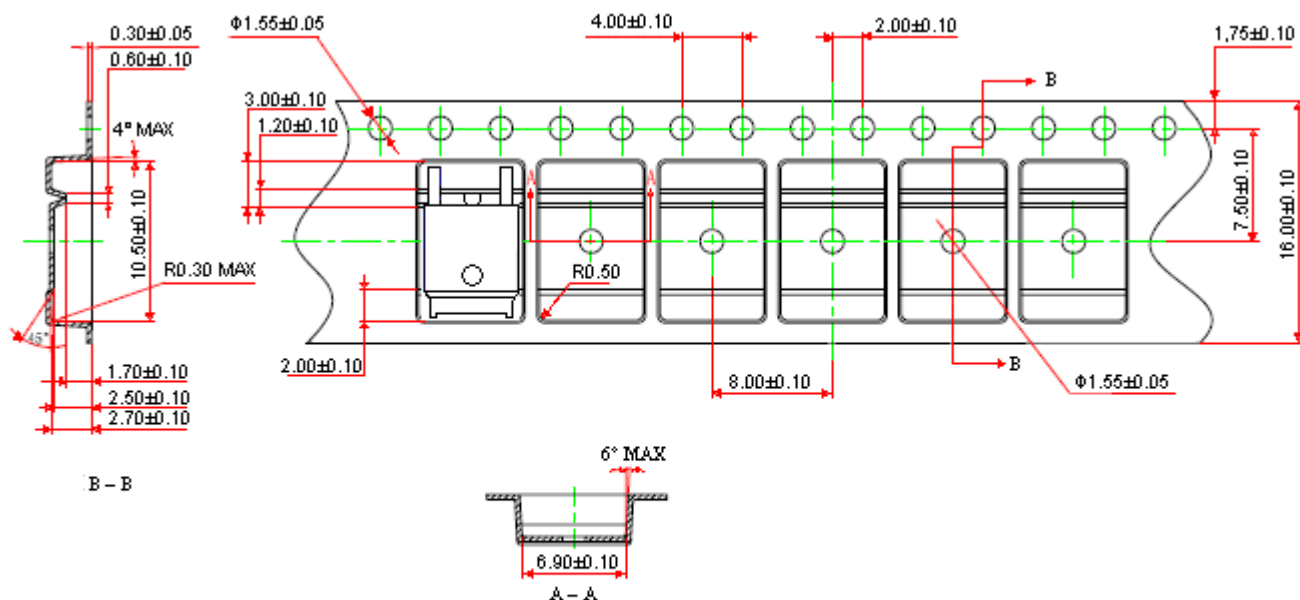
Transient Thermal Response Curves



Reel Dimension



Carrier Tape Dimension

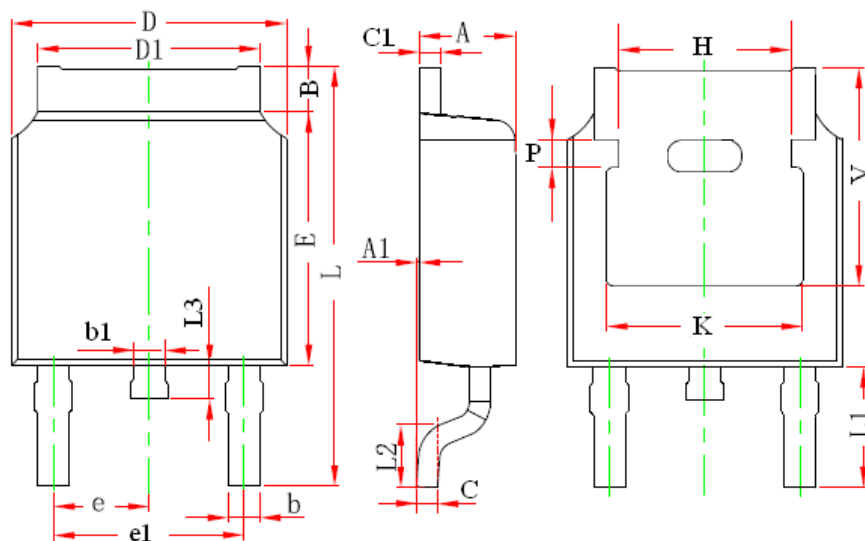


Notes:

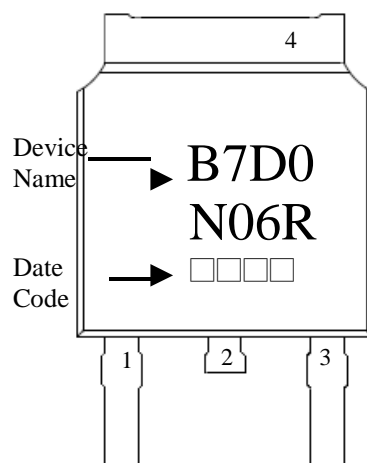
1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
2. Camber not to exceed 1mm in 100mm.
3. Material: conductive black polystyrene, antistatic coated : $10^5 \Omega/\square \sim 10^{11} \Omega/\square$

unit : mm

TO-252 Dimension



Marking:



3-Lead TO-252 Plastic Surface Mount Package

Style: Pin 1.Gate 2.Drain 3.Source
4.Drain

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF